



2SD882SS

NPN SILICON TRANSISTOR

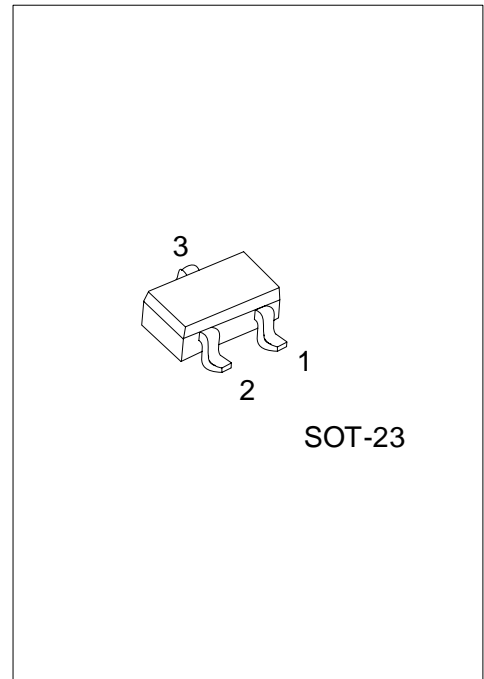
MEDIUM POWER LOW VOLTAGE TRANSISTOR

FEATURES

- * High current output up to 3A
- * Low saturation voltage
- * Complement to 2SB772SS

APPLICATIONS

- * Audio power amplifier
- * DC-DC convertor
- * Voltage regulator



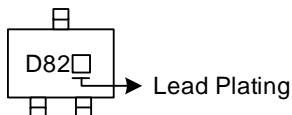
*Pb-free plating product number: 2SD882SSL

ORDERING INFORMATION

Order Number		Package	Pin Assignment			Packing
Normal	Lead Free Plating		1	2	3	
2SD882SS -x-AE3-R	2SD882SSL-x-AE3-R	SOT-23	E	B	C	Tape Reel

<p>2SD882SSL-x-AE3-R</p> <p>(1) Packing Type (2) Package Type (3) Rank (4) Lead Plating</p>	<p>(1) R: Tape Reel (2) AE3: SOT-23 (3) x: refer to Classification of h_{FE2} (4) L: Lead Free Plating, Blank: Pb/Sn</p>
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MARKING



■ ABSOLUTE MAXIMUM RATING (Ta=25 , unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Base Voltage	V _{CBO}	40	V
Collector-Emitter Voltage	V _{CEO}	30	V
Emitter-Base Voltage	V _{EBO}	5	V
Collector Current	DC	I _C	3
	Pulse	I _{CP}	7
Base Current	I _B	0.6	A
Collector Dissipation	Ta=25	P _C	1
	Tc=25		10
Junction Temperature	T _J	+150	
Storage Temperature	T _{STG}	-55 ~ +150	

Note Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (Ta=25 , unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV _{CBO}	I _C =100μA, I _E =0	40			V
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _C =1mA, I _B =0	30			V
Emitter-Base Breakdown Voltage	BV _{EBO}	I _E =100μA, I _C =0	5			V
Collector Cut-off Current	I _{CBO}	V _{CB} =30V, I _E =0			1000	nA
Emitter Cut-off Current	I _{EBO}	V _{EB} =3V, I _C =0			1000	nA
DC Current Gain (Note 1)	h _{FE1}	V _{CE} =2V, I _C =20mA	30	200		
	h _{FE2}	V _{CE} =2V, I _C =1A	100	150	400	
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	I _C =2A, I _B =0.2A		0.3	0.5	V
Base-Emitter Saturation Voltage	V _{BE(SAT)}	I _C =2A, I _B =0.2A		1.0	2.0	V
Current Gain Bandwidth Product	f _T	V _{CE} =5V, I _C =0.1A		80		MHz
Output Capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=1MHz		45		pF

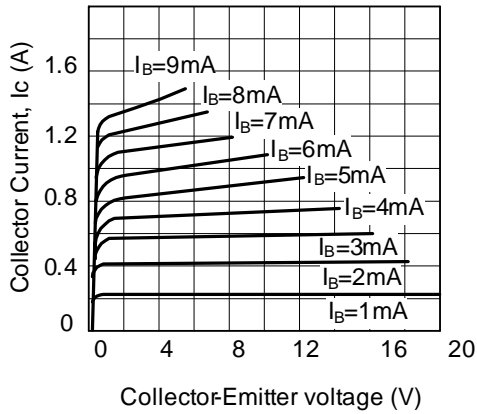
Note 1: Pulse test: PW<300μs, Duty Cycle<2%

■ CLASSIFICATION OF h_{FE2}

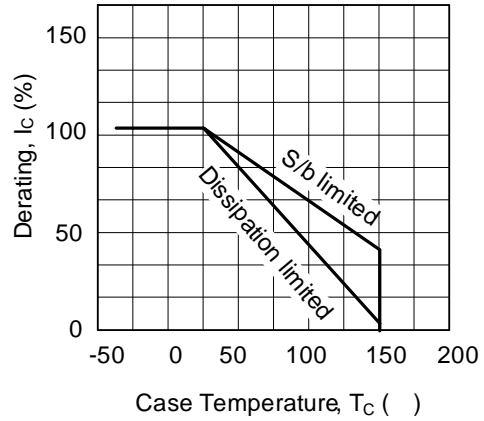
RANK	Q	P	E
RANGE	100-200	160-320	200-400

■ TYPICAL CHARACTERISTICS

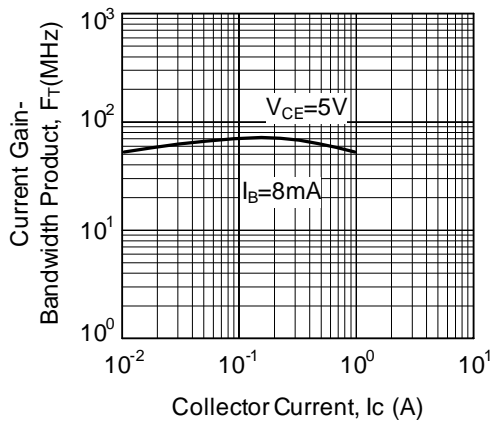
Static Characteristics



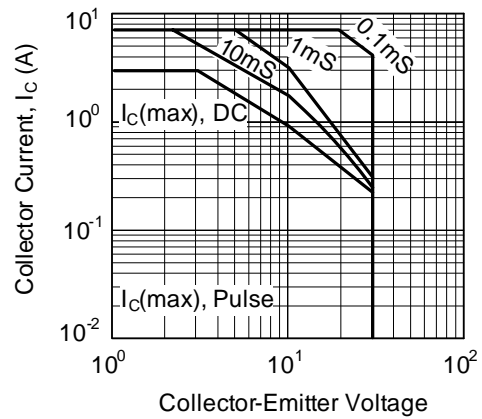
Derating Curve of Safe Operating Areas



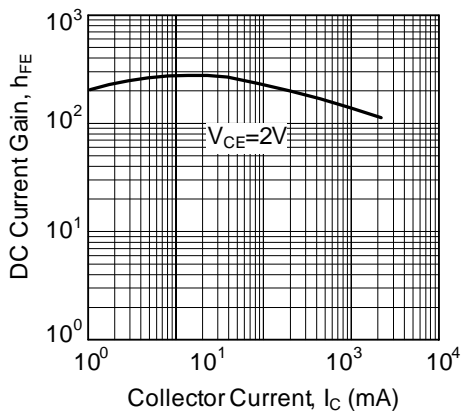
Current Gain-Bandwidth Product



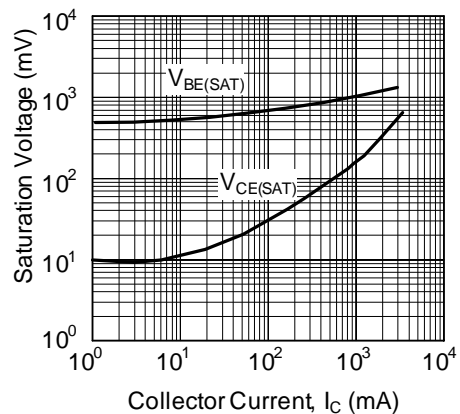
Safe Operating Area



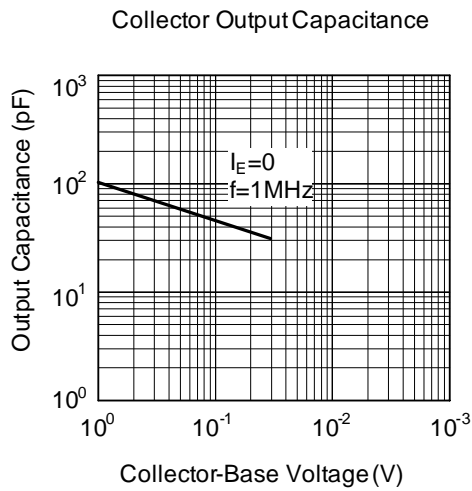
DC Current Gain



Saturation Voltage



■ TYPICAL CHARACTERISTICS(Cont.)



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